

INTEGRATED CIRCUITS

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

HEF4016B gates Quadruple bilateral switches

Product specification

File under Integrated Circuits, IC04

January 1995

Quadruple bilateral switches

**HEF4016B
gates**

DESCRIPTION

The HEF4016B has four independent analogue switches (transmission gates). Each switch has two input/output terminals (Y/Z) and an active HIGH enable input (E). When E is connected to V_{DD} a low impedance bidirectional path between Y and Z is established (ON condition). When E is connected to V_{SS} the switch is disabled and a high

impedance between Y and Z is established (OFF condition). Current through a switch will not cause additional V_{DD} current provided the voltage at the terminals of the switch is maintained within the supply voltage range; $V_{DD} \geq (V_Y, V_Z) \geq V_{SS}$. Inputs Y and Z are electrically equivalent terminals.

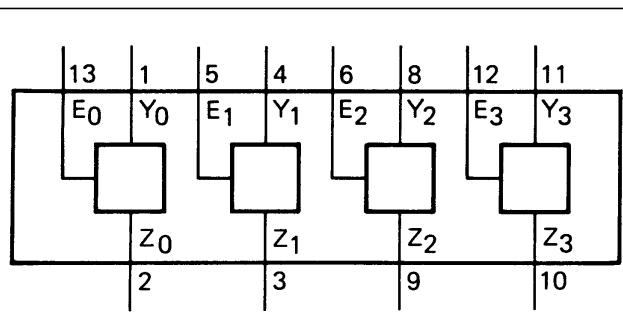


Fig.1 Functional diagram.

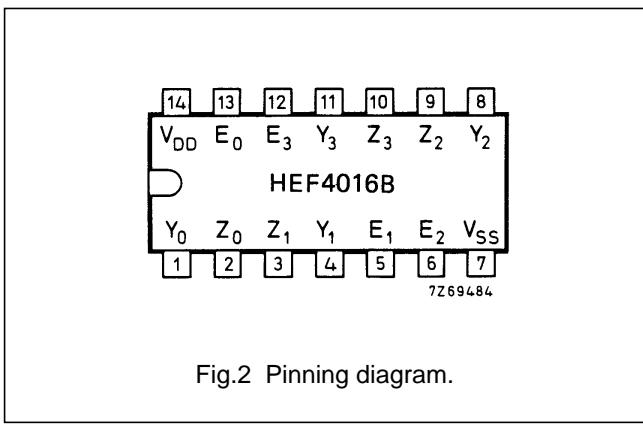


Fig.2 Pinning diagram.

PINNING

- E₀ to E₃ enable inputs
- Y₀ to Y₃ input/output terminals
- Z₀ to Z₃ input/output terminals

HEF4016BP(N): 14-lead DIL; plastic (SOT27-1)
HEF4016BD(F): 14-lead DIL; ceramic (cerdip) (SOT73)
HEF4016BT(D): 14-lead SO; plastic (SOT108-1)
(): Package Designator North America

APPLICATION INFORMATION

Some examples of applications for the HEF4016B are:

- Signal gating
- Modulation
- Demodulation
- Chopper

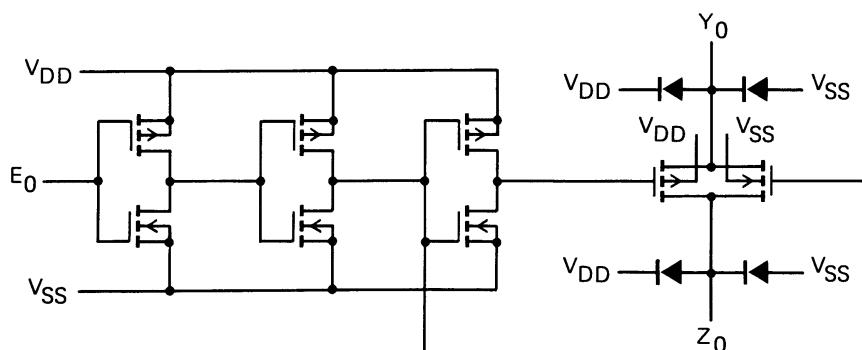


Fig.3 Schematic diagram (one switch).

Quadruple bilateral switches

HEF4016B
gates**RATINGS**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

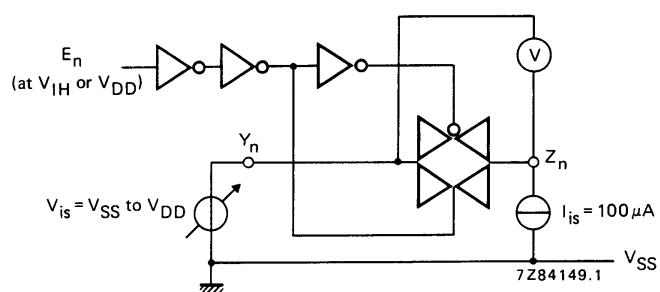
Power dissipation per switch	P	max.	100	mW
For other RATINGS see Family Specifications				

DC CHARACTERISTICS $T_{amb} = 25^\circ C$; $V_{SS} = 0 V$ (unless otherwise specified)

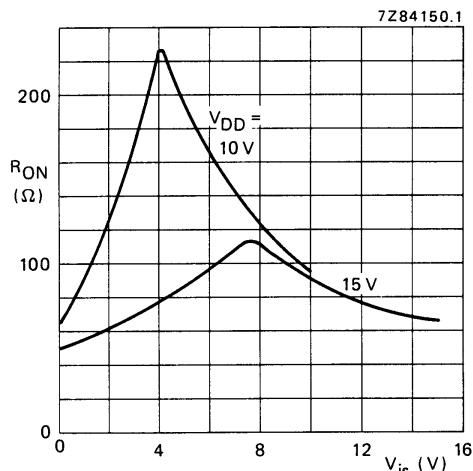
PARAMETER	V_{DD} V	SYMBOL	TYP.	MAX.	UNIT	CONDITIONS
ON resistance	5	R_{ON}	8000	—	Ω	E_n at V_{IH} ; $V_{is} = 0$ to V_{DD} ; see Fig.4
	10		230	690	Ω	
	15		115	350	Ω	
ON resistance	5	R_{ON}	140	425	Ω	E_n at V_{IH} ; $V_{is} = V_{SS}$; see Fig.4
	10		65	195	Ω	
	15		50	145	Ω	
ON resistance	5	R_{ON}	170	515	Ω	E_n at V_{IH} ; $V_{is} = V_{DD}$; see Fig.4
	10		95	285	Ω	
	15		75	220	Ω	
'Δ' ON resistance between any two channels	5	ΔR_{ON}	200	—	Ω	E_n at V_{IH} ; $V_{is} = 0$ to V_{DD} ; see Fig.4
	10		15	—	Ω	
	15		10	—	Ω	

PARAMETER	V_{DD} V	SYMBOL	$T_{amb} (^\circ C)$						UNIT	CONDITION
			-40	+25	+85	MIN.	MAX.	MIN.	MAX.	
Quiescent device current	5	I_{DD}	—	1,0	—	1,0	—	7,5	μA	$V_{SS} = 0$; all valid input combinations; $V_I = V_{SS}$ or V_{DD}
	10		—	2,0	—	2,0	—	15,0	μA	
	15		—	4,0	—	4,0	—	30,0	μA	
Input leakage current at E_n	15	$\pm I_{IN}$	—	—	—	300	—	1000	nA	E_n at V_{SS} or V_{DD}
OFF-state leakage current, any channel OFF	5	I_{OZ}	—	—	—	—	—	—	nA	E_n at V_{IL} ; $V_{is} = V_{SS}$ or V_{DD} ; $V_{os} = V_{DD}$ or V_{SS}
	10		—	—	—	—	—	—	nA	
	15		—	—	—	200	—	—	nA	
E_n input voltage LOW	5	V_{IL}	—	1,5	—	1,5	—	1,5	V	switch OFF; see Fig.9 for I_{OZ}
	10		—	3,0	—	3,0	—	3,0	V	
	15		—	4,0	—	4,0	—	4,0	V	
E_n input voltage HIGH	5	V_{IH}	3,5	—	3,5	—	3,5	—	V	low-impedance between Y and Z (ON condition) see R_{ON} switch
	10		7,0	—	7,0	—	7,0	—	V	
	15		11,0	—	11,0	—	11,0	—	V	

Quadruple bilateral switches

HEF4016B
gatesFig.4 Test set-up for measuring R_{ON} .

$E_n > V_{IH}$
 $I_{is} = 100 \mu A$
 $V_{SS} = 0 V$

Fig.5 Typical R_{ON} as a function of input voltage.

Quadruple bilateral switches

HEF4016B
gates

AC CHARACTERISTICS

 $V_{SS} = 0 \text{ V}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$; input transition times $\leq 20 \text{ ns}$

	V_{DD} V	SYMBOL	TYP.	MAX.	
Propagation delays $V_{is} \rightarrow V_{os}$ HIGH to LOW	5	t_{PHL}	25	50	ns
	10		10	20	ns
	15		5	10	ns
LOW to HIGH	5	t_{PLH}	20	40	ns
	10		10	20	ns
	15		5	10	ns
Output disable times $E_n \rightarrow V_{os}$ HIGH	5	t_{PHZ}	90	130	ns
	10		80	110	ns
	15		75	100	ns
LOW	5	t_{PLZ}	85	120	ns
	10		75	100	ns
	15		75	100	ns
Output enable times $E_n \rightarrow V_{os}$ HIGH	5	t_{PZH}	40	80	ns
	10		20	40	ns
	15		15	30	ns
LOW	5	t_{PZL}	40	80	ns
	10		20	40	ns
	15		15	30	ns
Distortion, sine-wave response	5		–	%	
	10		0,08	%	note 3
	15		0,04	%	
Crosstalk between any two channels	5		–	MHz	
	10		1	MHz	note 4
	15		–	MHz	
Crosstalk; enable input to output	5		–	mV	
	10		50	mV	note 5
	15		–	mV	
OFF-state feed-through	5		–	MHz	
	10		1	MHz	note 6
	15		–	MHz	
ON-state frequency response	5		–	MHz	
	10		90	MHz	note 7
	15		–	MHz	

Quadruple bilateral switches

**HEF4016B
gates**

Notes

V_{is} is the input voltage at a Y or Z terminal, whichever is assigned as input.

V_{os} is the output voltage at a Y or Z terminal, whichever is assigned as output.

1. $R_L = 10 \text{ k}\Omega$ to V_{SS} ; $C_L = 50 \text{ pF}$ to V_{SS} ; $E_n = V_{DD}$; $V_{is} = V_{DD}$ (square-wave); see Figs 6 and 10.
2. $R_L = 10 \text{ k}\Omega$; $C_L = 50 \text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave);
 $V_{is} = V_{DD}$ and R_L to V_{SS} for t_{PHZ} and t_{PZH} ;
 $V_{is} = V_{SS}$ and R_L to V_{DD} for t_{PLZ} and t_{PZL} ; see Figs 6 and 11.
3. $R_L = 10 \text{ k}\Omega$; $C_L = 15 \text{ pF}$; $E_n = V_{DD}$; $V_{is} = 1/2V_{DD(p-p)}$ (sine-wave, symmetrical about $1/2V_{DD}$);
 $f_{is} = 1 \text{ kHz}$; see Fig.7.
4. $R_L = 1 \text{ k}\Omega$; $V_{is} = 1/2V_{DD(p-p)}$ (sine-wave, symmetrical about $1/2V_{DD}$);

$$20 \log \frac{V_{os} (\text{B})}{V_{is} (\text{A})} = -50 \text{ dB}; E_n (\text{A}) = V_{SS}; E_n (\text{B}) = V_{DD}; \text{see Fig. 8.}$$

5. $R_L = 10 \text{ k}\Omega$ to V_{SS} ; $C_L = 15 \text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave); crosstalk is $|V_{os}|$ (peak value);
see Fig.6.
6. $R_L = 1 \text{ k}\Omega$; $C_L = 5 \text{ pF}$; $E_n = V_{SS}$; $V_{is} = 1/2V_{DD(p-p)}$ (sine-wave, symmetrical about $1/2V_{DD}$);

$$20 \log \frac{V_{os}}{V_{is}} = -50 \text{ dB}; \text{see Fig. 7.}$$

7. $R_L = 1 \text{ k}\Omega$; $C_L = 5 \text{ pF}$; $E_n = V_{DD}$; $V_{is} = 1/2V_{DD(p-p)}$ (sine-wave, symmetrical about $1/2V_{DD}$);

$$20 \log \frac{V_{os}}{V_{is}} = -3 \text{ dB}; \text{see Fig. 7.}$$

	$\frac{V_{DD}}{V}$	TYPICAL FORMULA FOR P (μW)	
Dynamic power dissipation per package (P) ⁽¹⁾	5 10 15	$550 f_i + \sum (f_o C_L) \times V_{DD}^2$ $2\ 600 f_i + \sum (f_o C_L) \times V_{DD}^2$ $6\ 500 f_i + \sum (f_o C_L) \times V_{DD}^2$	where f_i = input freq. (MHz) f_o = output freq. (MHz) C_L = load capacitance (pF) $\sum (f_o C_L)$ = sum of outputs V_{DD} = supply voltage (V)

Note

1. All enable inputs switching.

Quadruple bilateral switches

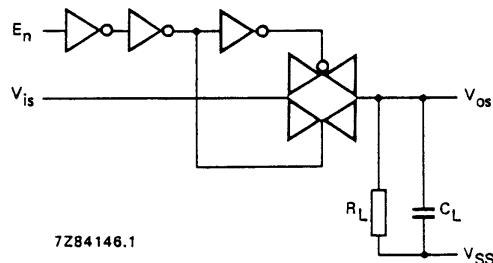
HEF4016B
gates

Fig.6

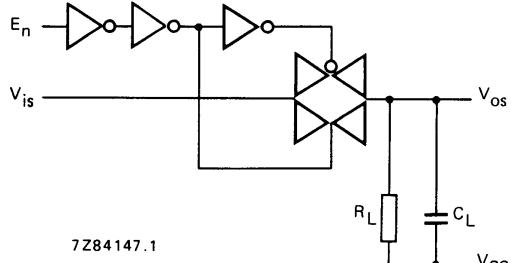
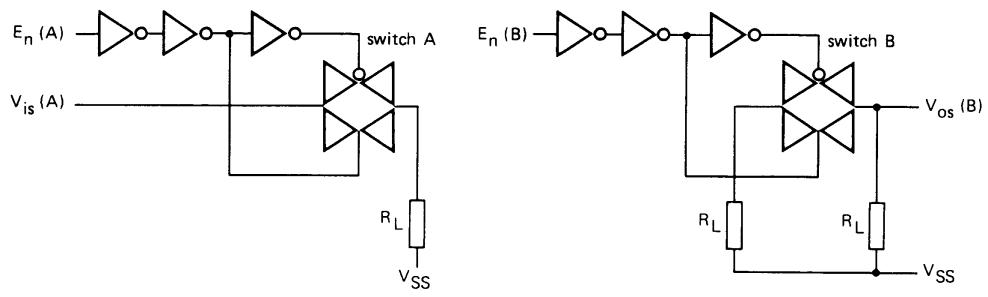


Fig.7



(a)

(b)

Fig.8

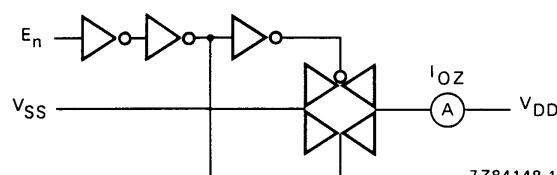
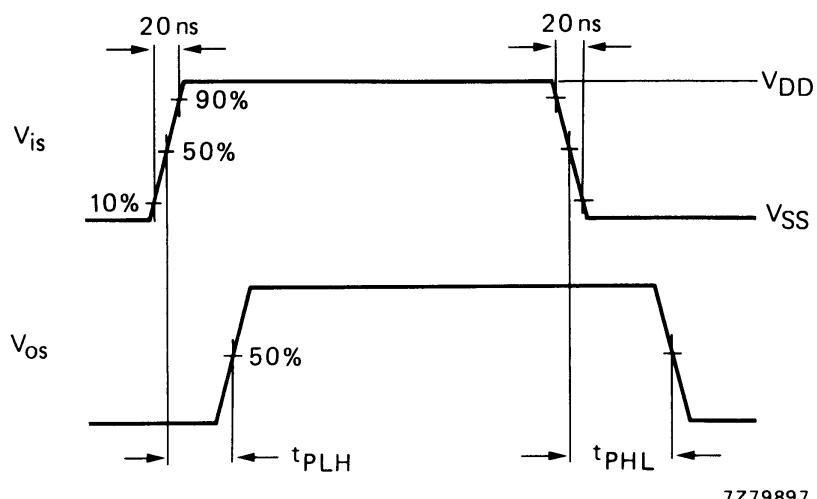
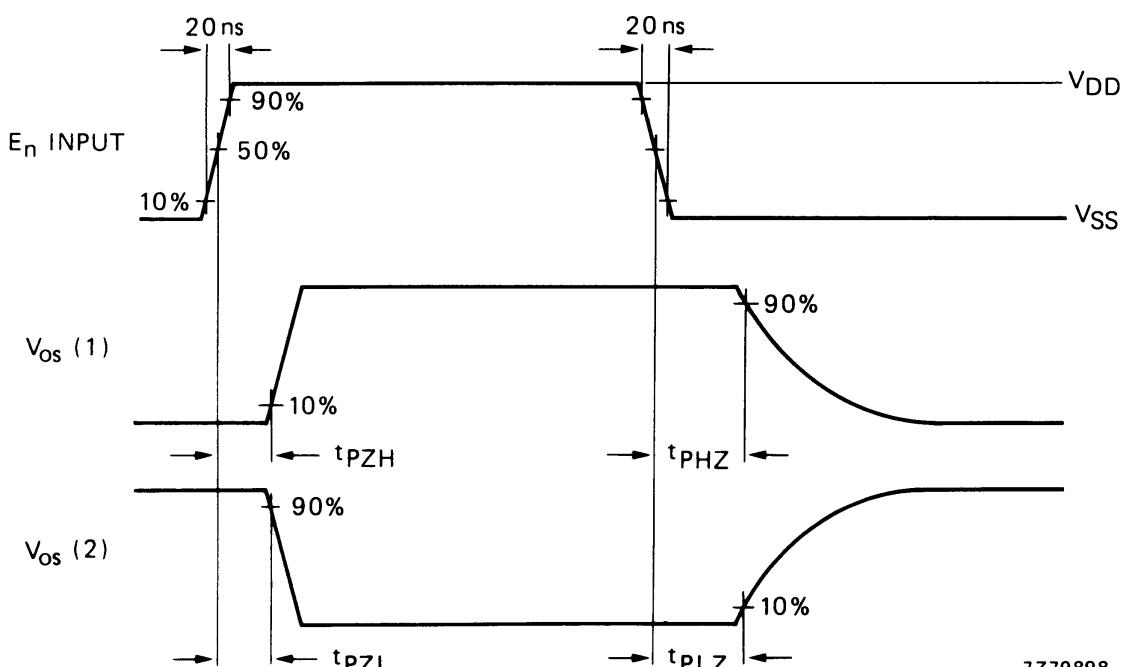


Fig.9

Quadruple bilateral switches

HEF4016B
gatesFig.10 Waveforms showing propagation delays from V_{is} to V_{os} .

- (1) V_{is} at V_{DD}
- (2) V_{is} at V_{SS}

Fig.11 Waveforms showing output disable and enable times.